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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	50MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LVD, PWM, WDT
Number of I/O	54
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 22x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08qe96clh

Part Number	Package Description	Original (gold wire) package document number	Current (copper wire) package document number
MC68HC908JW32	48 QFN	98ARH99048A	98ASA00466D
MC9S08AC16			
MC9S908AC60			
MC9S08AC128			
MC9S08AW60			
MC9S08GB60A			
MC9S08GT16A			
MC9S08JM16			
MC9S08JM60			
MC9S08LL16			
MC9S08QE128			
MC9S08QE32			
MC9S08RG60			
MCF51CN128			
MC9RS08LA8	48 QFN	98ARL10606D	98ASA00466D
MC9S08GT16A	32 QFN	98ARH99035A	98ASA00473D
MC9S908QE32	32 QFN	98ARE10566D	98ASA00473D
MC9S908QE8	32 QFN	98ASA00071D	98ASA00736D
MC9S08JS16	24 QFN	98ARL10608D	98ASA00734D
MC9S08QB8			
MC9S08QG8	24 QFN	98ARL10605D	98ASA00474D
MC9S08SH8	24 QFN	98ARE10714D	98ASA00474D
MC9RS08KB12	24 QFN	98ASA00087D	98ASA00602D
MC9S08QG8	16 QFN	98ARE10614D	98ASA00671D
MC9RS08KB12	8 DFN	98ARL10557D	98ASA00672D
MC9S08QG8			
MC9RS08KA2	6 DFN	98ARL10602D	98ASA00735D

1 MC9S08QE128 Series Comparison

The following table compares the various device derivatives available within the MC9S08QE128 series.

Table 1. MC9S08QE128 Series Features by MCU and Package

Feature	MC9S08QE128				MC9S08QE96				MC9S08QE64			
Flash size (bytes)	131072				98304				65536			
RAM size (bytes)	8064				6016				4096			
Pin quantity	80	64	48	44	80	64	48	44	64	48	44	32
ACMP1	yes											
ACMP2	yes											
ADC channels	24	22	10	10	24	22	10	10	22	10	10	10
DBG	yes											
ICS	yes											
IIC1	yes											
IIC2	yes	yes	no	no	yes	yes	no	no	yes	no	no	no
IRQ	yes											
KBI	16	16	16	16	16	16	16	16	16	16	16	12
Port I/O[1]	70	54	38	34	70	54	38	34	54	38	34	26
RTC	yes											
SCI1	yes											
SCI2	yes											
SPI1	yes											
SPI2	yes											
TPM1 channels	3											
TPM2 channels	3											
TPM3 channels	6											
XOSC	yes											

[1] Port I/O count does not include the input only PTA5/IRQ/TPM1CLK/$\overline{\text{RESET}}$ or the output only PTA4/ACMP1O/BKGD/MS.

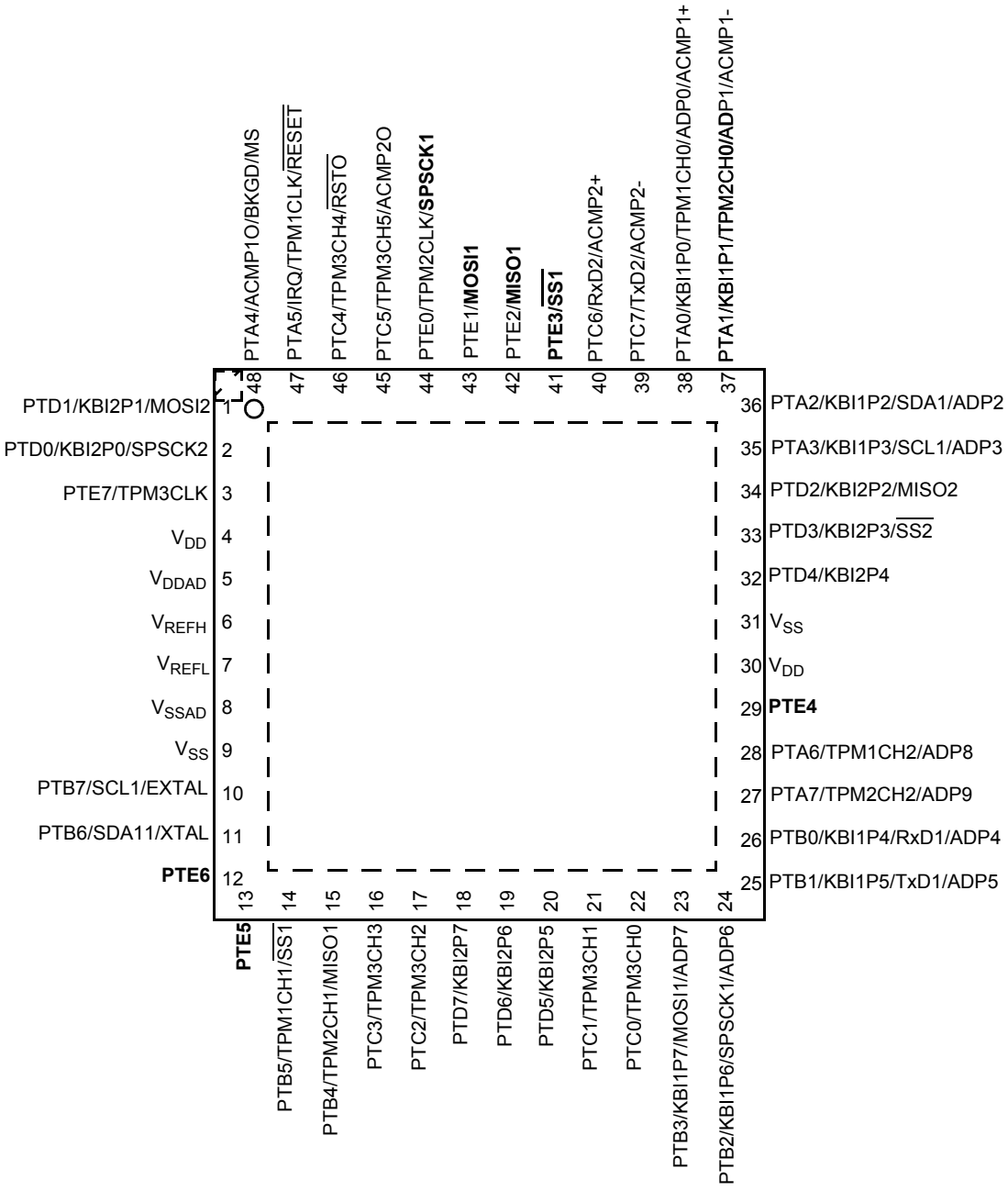


Figure 4. Pin Assignments in 48-Pin QFN Package

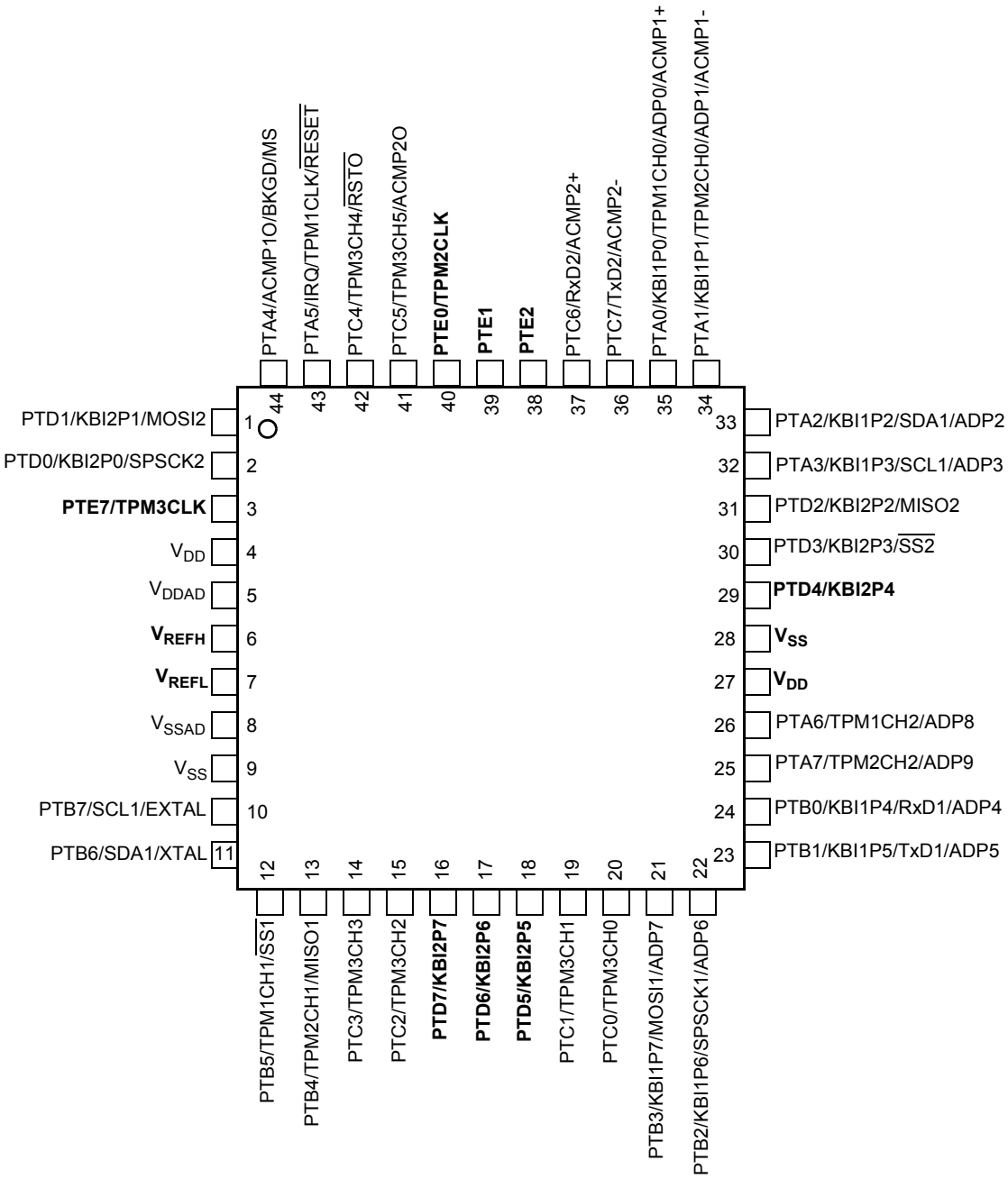


Figure 5. Pin Assignments in 44-Pin LQFP Package

[3] Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

3.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 5. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	–40 to 85	°C
Maximum junction temperature	T_{JM}	95	°C
Thermal resistance Single-layer board			
32-pin LQFP	θ_{JA}	82	°C/W
44-pin LQFP		68	
48-pin QFN		81	
64-pin LQFP	θ_{JA}	69	°C/W
80-pin LQFP		60	
Thermal resistance Four-layer board			
32-pin LQFP	θ_{JA}	54	°C/W
44-pin LQFP		46	
48-pin QFN		26	
64-pin LQFP	θ_{JA}	50	°C/W
80-pin LQFP		47	

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \qquad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C
θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W
$P_D = P_{int} + P_{I/O}$
$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power
$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 6. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	3	
Machine	Series resistance	R1	0	Ω
	Storage capacitance	C	200	pF
	Number of pulses per pin	—	3	
Latch-up	Minimum input voltage limit		– 2.5	V
	Maximum input voltage limit		7.5	V

Table 7. ESD and Latch-Up Protection Characteristics

No.	Rating[1]	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	± 2000	—	V
2	Machine model (MM)	V_{MM}	± 200	—	V
3	Charge device model (CDM)	V_{CDM}	± 500	—	V
4	Latch-up current at T_A = 85°C	I_{LAT}	± 100	—	mA

1 Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

3.6 DC Characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 8. DC Characteristics

Num	C	Characteristic	Symbol	Condition	Min	Typ[1]	Max	Unit
1		Operating Voltage			1.8[2]		3.6	V
2	C	Output high voltage — All I/O pins, low-drive strength	V_{OH}	1.8 V, I_{Load} = –2 mA	V_{DD} – 0.5	—	—	V
	P	Output high voltage — All I/O pins, high-drive strength		2.7 V, I_{Load} = –10 mA	V_{DD} – 0.5	—	—	
	T			2.3 V, I_{Load} = –6 mA	V_{DD} – 0.5	—	—	
	C			1.8V, I_{Load} = –3 mA	V_{DD} – 0.5	—	—	
3	D	Output high current — Max total I_{OH} for all ports	I_{OHT}		—	—	100	mA
4	C	Output low voltage — All I/O pins, low-drive strength	V_{OL}	1.8 V, I_{Load} = 2 mA	—	—	0.5	V
	P	Output low voltage — All I/O pins, high-drive strength		2.7 V, I_{Load} = 10 mA	—	—	0.5	
	T			2.3 V, I_{Load} = 6 mA	—	—	0.5	
	C			1.8 V, I_{Load} = 3 mA	—	—	0.5	
5	D	Output low current — Max total I_{OL} for all ports	I_{OLT}		—	—	100	mA
6	P	Input high voltage — all digital inputs	V_{IH}	V_{DD} > 2.7 V	0.70 x V_{DD}	—	—	V
	C			V_{DD} > 1.8 V	0.85 x V_{DD}	—	—	
7	P	Input low voltage — all digital inputs	V_{IL}	V_{DD} > 2.7 V	—	—	0.35 x V_{DD}	
	C			V_{DD} >1.8 V	—	—	0.30 x V_{DD}	
8	C	Input hysteresis — all digital inputs	V_{hys}		0.06 x V_{DD}	—	—	mV
9	P	Input leakage current — all input only pins (Per pin)	$\|I_{In}\|$	V_{In} = V_{DD} or V_{SS}	—	—	1	µA
10	P	Hi-Z (off-state) leakage current — all input/output (per pin)	$\|I_{OZ}\|$	V_{In} = V_{DD} or V_{SS}	—	—	1	µA
11	P	Pull-up resistors — all digital inputs, when enabled	R_{PU}		17.5	—	52.5	kΩ
12	D	DC injection current [3, 4, 5] — Single pin limit	I_{IC}	V_{IN} < V_{SS}, V_{IN} > V_{DD}	–0.2	—	0.2	mA
		DC injection current [3, 4, 5] — Total MCU limit, includes sum of all stressed pins			–5	—	5	mA
13	C	Input Capacitance, all pins	C_{In}		—	—	8	pF
14	C	RAM retention voltage	V_{RAM}		—	0.6	1.0	V
15	C	POR re-arm voltage[6]	V_{POR}		0.9	1.4	1.79	V
16	D	POR re-arm time	t_{POR}		10	—	—	µs
17	P	Low-voltage detection threshold — high range[7]	V_{LVDH}[8]	V_{DD} falling V_{DD} rising	2.11 2.16	2.16 2.21	2.22 2.27	V

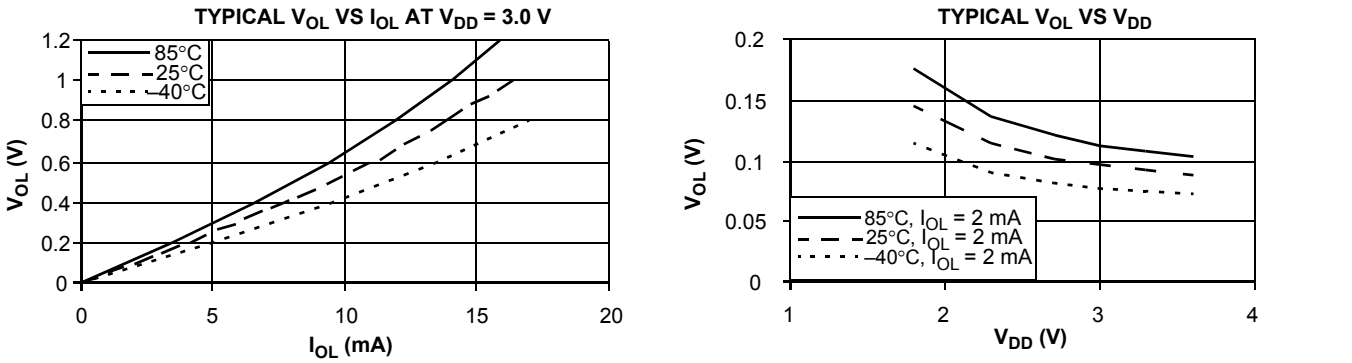


Figure 8. Typical Low-Side Driver (Sink) Characteristics — Low Drive (PTxDSn = 0)

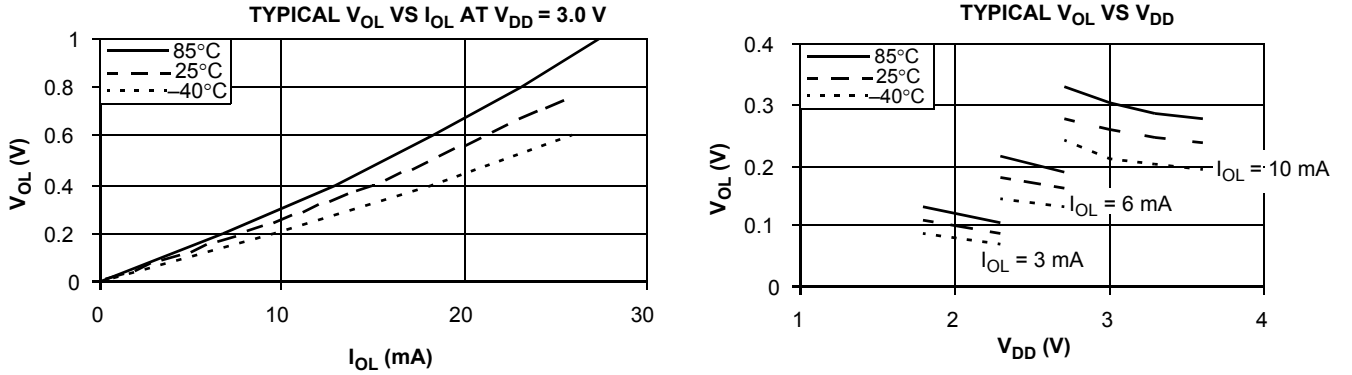


Figure 9. Typical Low-Side Driver (Sink) Characteristics — High Drive (PTxDSn = 1)

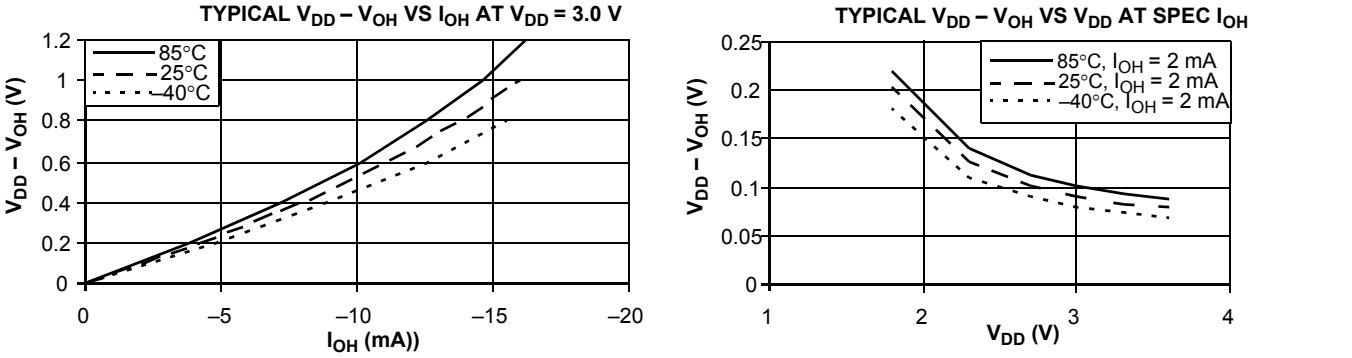


Figure 10. Typical High-Side (Source) Characteristics — Low Drive (PTxDSn = 0)

Table 9. Supply Current Characteristics (continued)

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)
6	P	Stop2 mode supply current	$S2I_{DD}$	n/a	3	0.35	0.6	μA	-40 to 25
	C					0.98	2.0		70
	P					2.5	7.5		85
	C				2	0.25	0.5		-40 to 25
	C					1.4	1.9		70
	C					1.91	6.5		85
7	P	Stop3 mode supply current No clocks active	$S3I_{DD}$	n/a	3	0.45	1.0	μA	-40 to 25
	C					1.99	4.2		70
	P					5.0	15.0		85
	C				2	0.35	0.7		-40 to 25
	C					2.9	3.9		70
	C					3.77	13.2		85

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

Table 10. Stop Mode Adders

Num	C	Parameter	Condition	Temperature (°C)				Units
				-40	25	70	85	
1	T	LPO		50	75	100	150	nA
2	T	ERREFSTEN	RANGE = HGO = 0	1000	1000	1100	1500	nA
3	T	IREFSTEN[1]		63	70	77	81	uA
4	T	RTC	does not include clock source current	50	75	100	150	nA
5	T	LVD[1]	LVDSE = 1	90	100	110	115	uA
6	T	ACMP[1]	not using the bandgap (BGBE = 0)	18	20	22	23	uA
7	T	ADC[1]	ADLPC = ADLSMP = 1 not using the bandgap (BGBE = 0)	95	106	114	120	uA

1 Not available in stop2 mode.

3.8 External Oscillator (XOSC) Characteristics

Reference Figure 13 and Figure 14 for crystal or resonator circuits.

Table 11. XOSC and ICS Specifications (Temperature Range = –40 to 85°C Ambient)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
1	C	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) Low range (RANGE = 0) High range (RANGE = 1), high gain (HGO = 1) High range (RANGE = 1), low power (HGO = 0)	 f_{lo} f_{hi} f_{hi}	 32 1 1	 — — —	 38.4 16 8	 kHz MHz MHz
2	D	Load capacitors Low range (RANGE=0), low power (HGO=0) Other oscillator settings	C_1,C_2	See Note[2] See Note[3]			
3	D	Feedback resistor Low range, low power (RANGE=0, HGO=0)[2] Low range, High Gain (RANGE=0, HGO=1) High range (RANGE=1, HGO=X)	R_F	 — — —	 — 10 1	 — — —	MΩ
4	D	Series resistor — Low range, low power (RANGE = 0, HGO = 0)[2] Low range, high gain (RANGE = 0, HGO = 1) High range, low power (RANGE = 1, HGO = 0) High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	R_S	 — — — — — —	 — 0 100 0 0 0	 — — — 0 10 20	kΩ
5	C	Crystal start-up time [4] Low range, low power Low range, high power High range, low power High range, high power	 t_{CSTL} t_{CSTH} 	 — — — —	 200 400 5 15	 — — — —	ms
6	D	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE or FBE mode FBELP mode	f_{extal}	0.03125 0	— —	40.0 50.33	MHz MHz

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

2 Load capacitors (C_1,C_2), feedback resistor (R_F) and series resistor (R_S) are incorporated internally when RANGE=HGO=0.

3 See crystal or resonator manufacturer's recommendation.

4 Proper PC board layout procedures must be followed to achieve specifications.

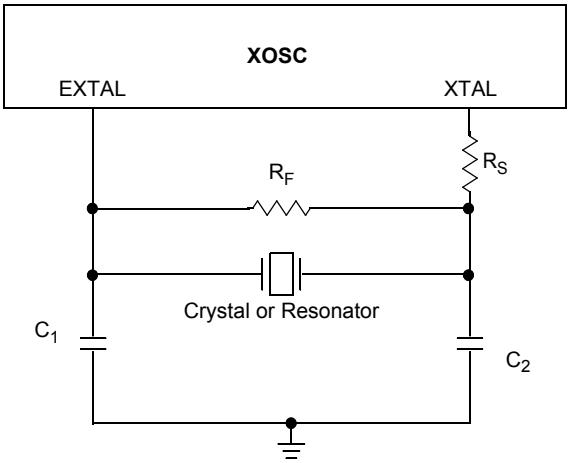


Figure 13. Typical Crystal or Resonator Circuit: High Range and Low Range/High Gain

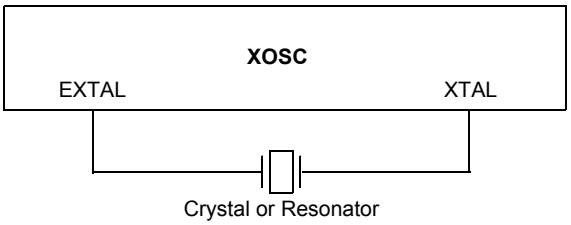


Figure 14. Typical Crystal or Resonator Circuit: Low Range/Low Gain

3.9 Internal Clock Source (ICS) Characteristics

Table 12. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient)

Num	C	Characteristic		Symbol	Min	Typ[1]	Max	Unit
1	P	Average internal reference frequency — factory trimmed at V_{DD} = 3.6 V and temperature = 25°C		f_{int_ft}	—	32.768	—	kHz
2	P	Internal reference frequency — user trimmed		f_{int_ut}	31.25	—	39.06	kHz
3	T	Internal reference start-up time		t_{IRST}	—	60	100	µs
4	P	DCO output frequency range — trimmed [2]	Low range (DRS=00)	f_{dco_u}	16	—	20	MHz
	P		Mid range (DRS=01)		32	—	40	
	P		High range (DRS=10)		48	—	60	
5	P	DCO output frequency [2] Reference = 32768 Hz and DMX32 = 1	Low range (DRS=00)	f_{dco_DMX32}	—	19.92	—	MHz
	P		Mid range (DRS=01)		—	39.85	—	
	P		High range (DRS=10)		—	59.77	—	
6	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco\_res\_t}$	—	± 0.1	± 0.2	$\%f_{dco}$
7	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco\_res\_t}$	—	± 0.2	± 0.4	$\%f_{dco}$

3.10.2 TPM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 14. TPM Input Timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

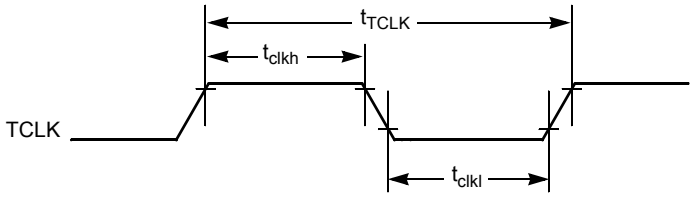


Figure 19. Timer External Clock

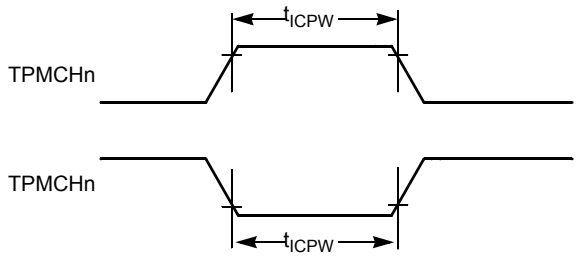


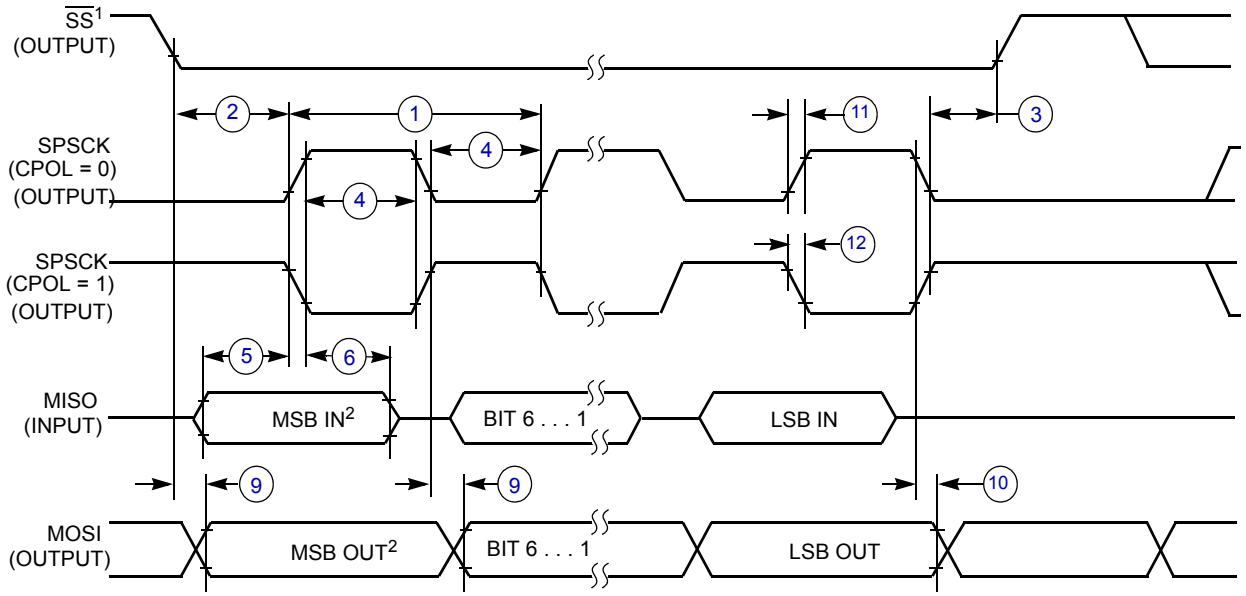
Figure 20. Timer Input Capture Pulse

3.10.3 SPI Timing

Table 15 and Figure 21 through Figure 24 describe the timing requirements for the SPI system.

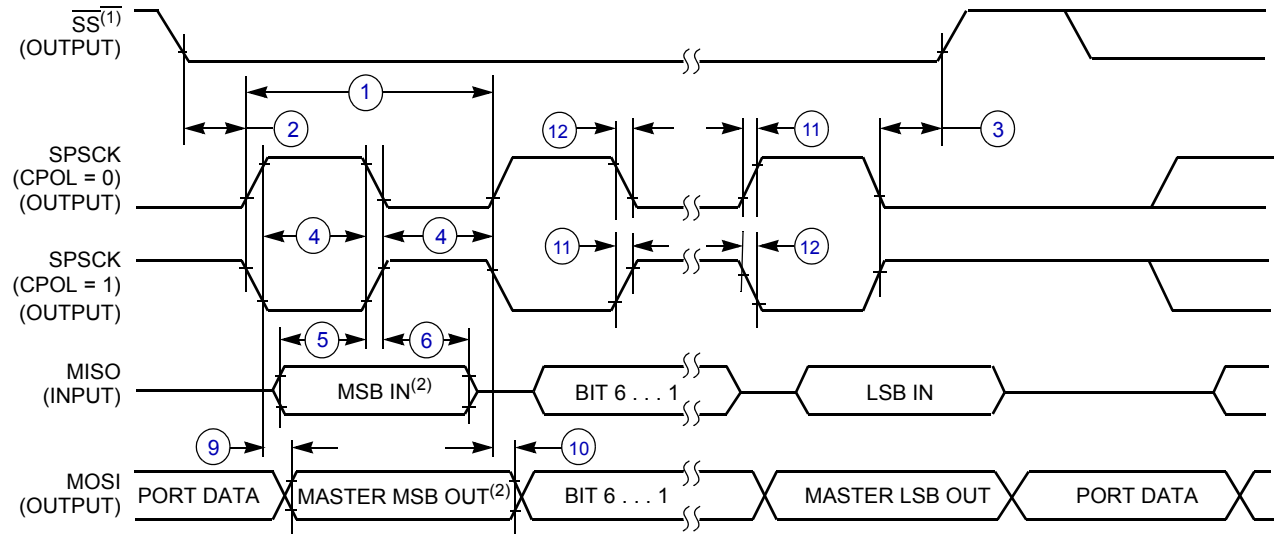
Table 15. SPI Timing

No.	C	Function	Symbol	Min	Max	Unit
—	D	Operating frequency Master Slave	f_{op}	 $f_{Bus}/2048$ 0	 $f_{Bus}/2$ $f_{Bus}/4$	 Hz Hz
1	D	SPSCK period Master Slave	t_{SPSCK}	 2 4	 2048 —	 t_{cyc} t_{cyc}
2	D	Enable lead time Master Slave	t_{Lead}	 1/2 1	 — —	 t_{SPSCK} t_{cyc}
3	D	Enable lag time Master Slave	t_{Lag}	 1/2 1	 — —	 t_{SPSCK} t_{cyc}
4	D	Clock (SPSCK) high or low time Master Slave	t_{WSPSCK}	 $t_{cyc} - 30$ $t_{cyc} - 30$	 1024 t_{cyc} —	 ns ns
5	D	Data setup time (inputs) Master Slave	t_{SU}	 15 15	 — —	 ns ns
6	D	Data hold time (inputs) Master Slave	t_{HI}	 0 25	 — —	 ns ns
7	D	Slave access time	t_a	—	1	t_{cyc}
8	D	Slave MISO disable time	t_{dis}	—	1	t_{cyc}
9	D	Data valid (after SPSCK edge) Master Slave	t_v	 — —	 25 25	 ns ns
10	D	Data hold time (outputs) Master Slave	t_{HO}	 0 0	 — —	 ns ns
11	D	Rise time Input Output	 t_{RI} t_{RO}	 — —	 $t_{cyc} - 25$ 25	 ns ns
12	D	Fall time Input Output	 t_{FI} t_{FO}	 — —	 $t_{cyc} - 25$ 25	 ns ns



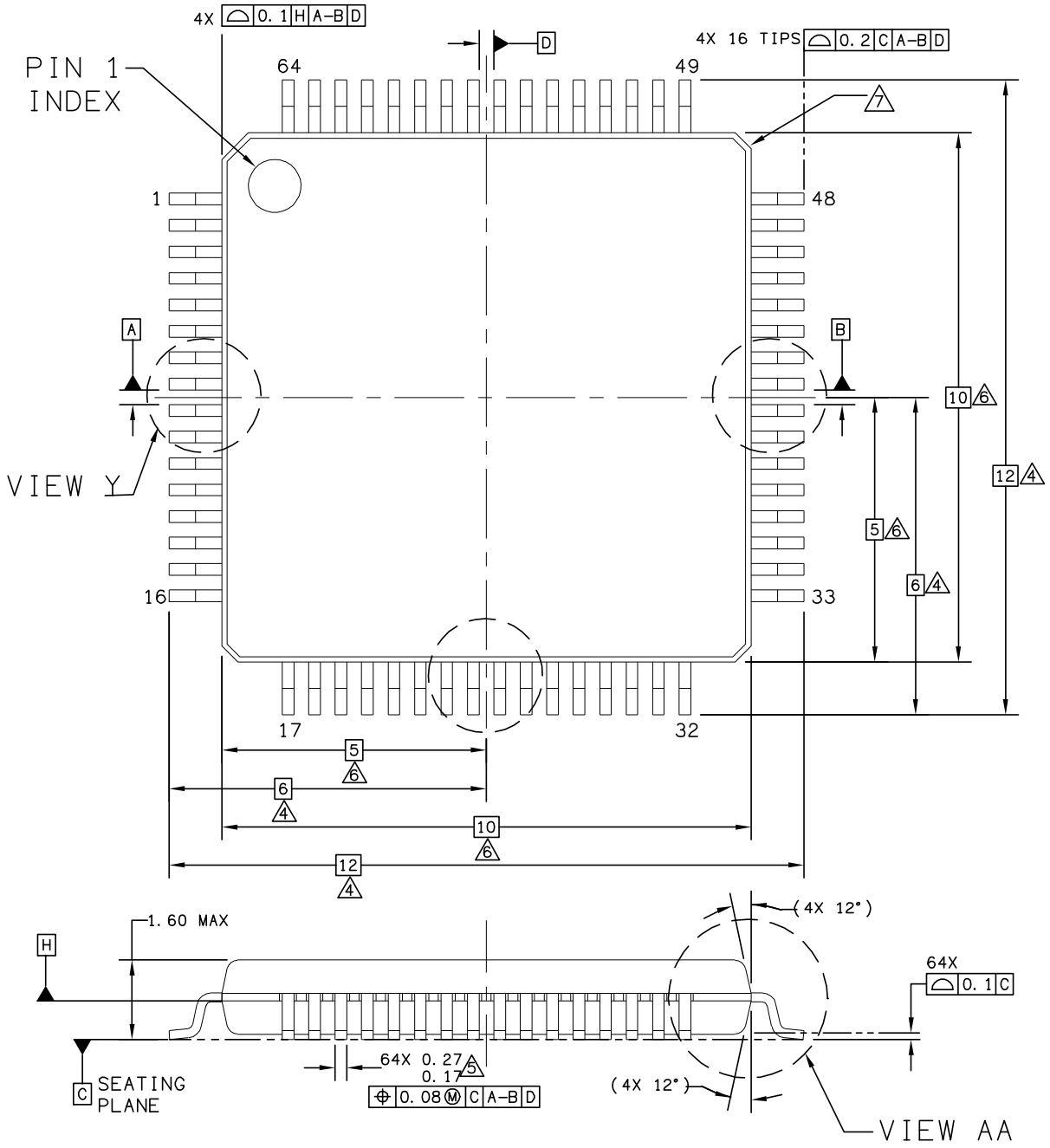
NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 21. SPI Master Timing (CPHA = 0)



NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 22. SPI Master Timing (CPHA =1)



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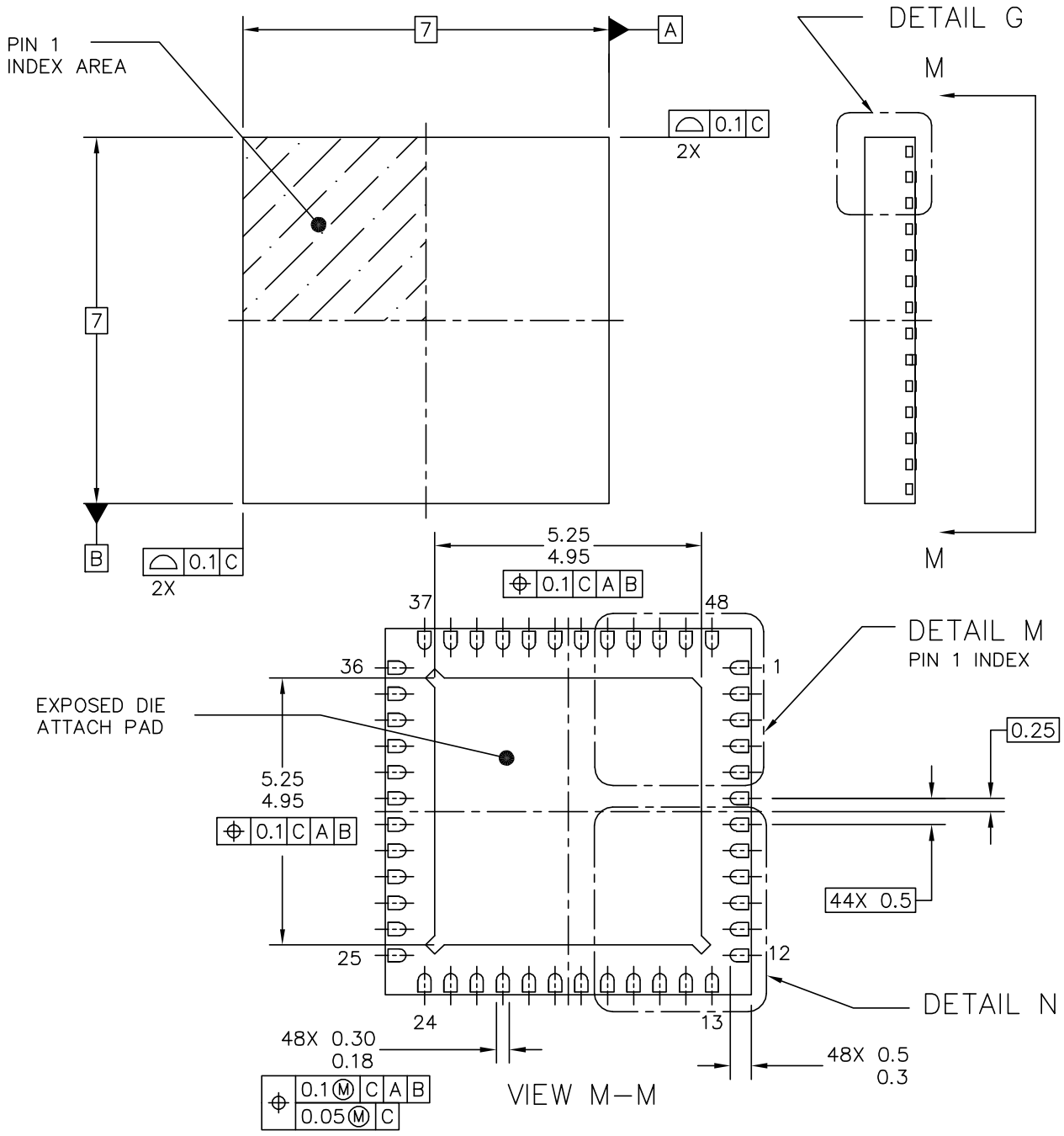
TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	DOCUMENT NO: 98ASS23234W	REV: D
	CASE NUMBER: 840F-02	06 APR 2005
	STANDARD: JEDEC MS-026 BCD	

Figure 27. 64-pin LQFP Package Drawing (Case 840F, Doc #98ASS23234W), Sheet 1 of 3



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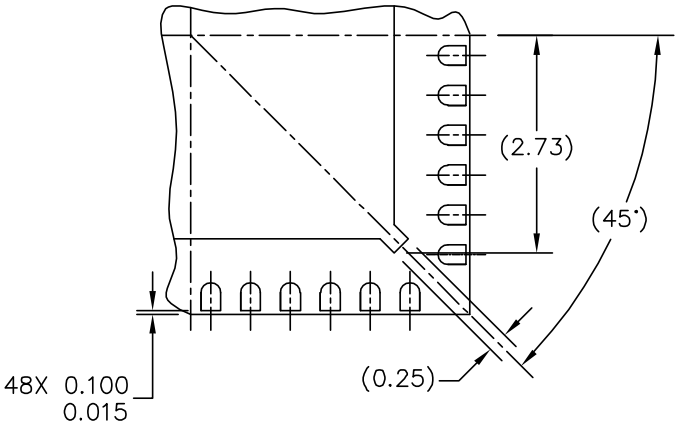
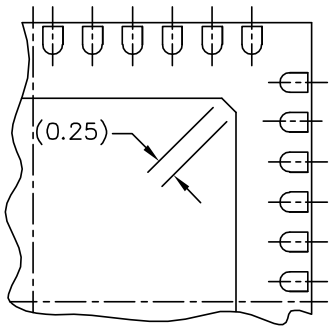
TITLE: THERMALLY ENHANCED QUAD FLAT NON–LEADED PACKAGE (QFN) 48 TERMINAL, 0.5 PITCH (7 X 7 X 1)	DOCUMENT NO: 98ARH99048A	REV: F
	CASE NUMBER: 1314–05	05 DEC 2005
	STANDARD: JEDEC–MO–220 VKKD–2	

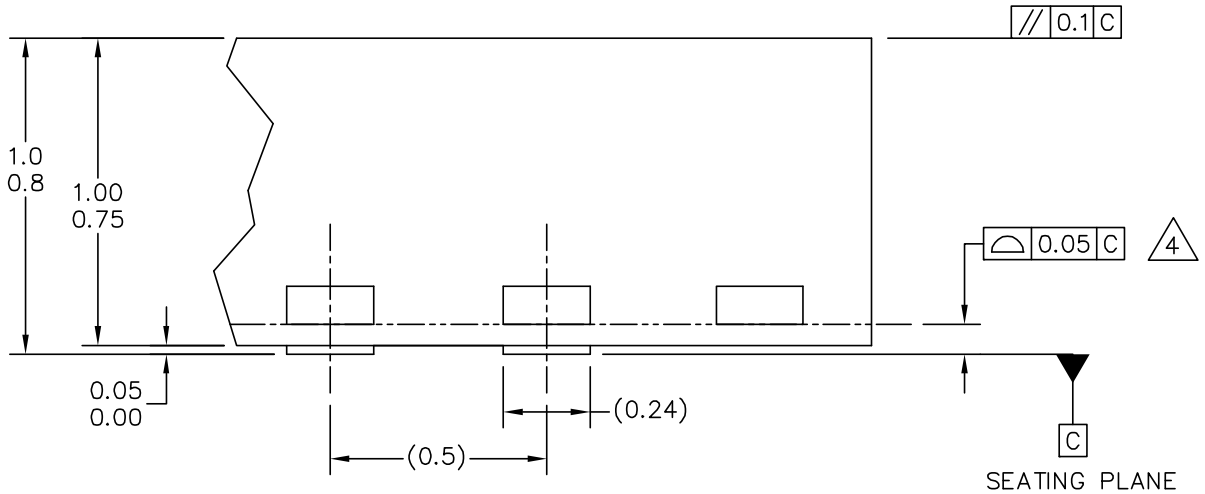
Figure 30. 48-pin QFN Package Drawing (Case 1314, Doc #98ARH99048A), Sheet 1 of 3



DETAIL N
PREFERRED CORNER CONFIGURATION



DETAIL M
PREFERED PIN 1 BACKSIDE IDENTIFIER



DETAIL G
VIEW ROTATED 90° CW

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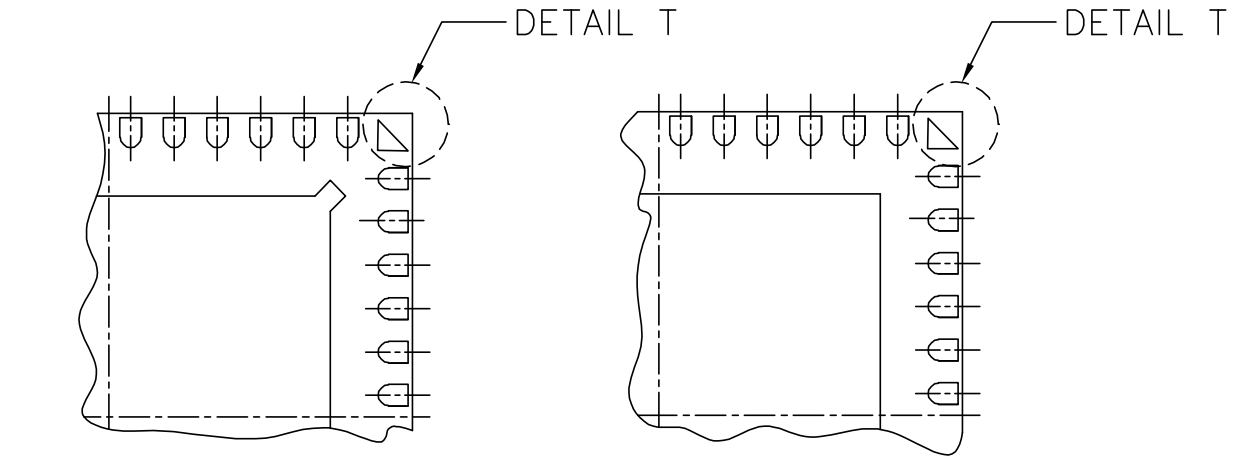
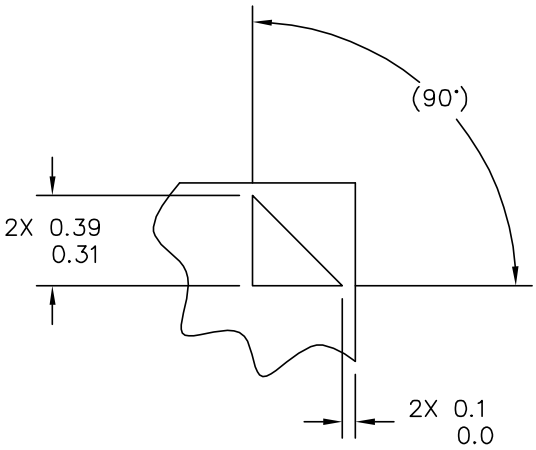
TITLE: THERMALLY ENHANCED QUAD FLAT NON–LEADED PACKAGE (QFN) 48 TERMINAL, 0.5 PITCH (7 X 7 X 1)	DOCUMENT NO: 98ARH99048A	REV: F
	CASE NUMBER: 1314–05	05 DEC 2005
	STANDARD: JEDEC–MO–220 VKKD–2	

Figure 31. 48-pin QFN Package Drawing (Case 1314, Doc #98ARH99048A), Sheet 2 of 3





NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.
3. THE COMPLETE JEDEC DESIGNATOR FOR THIS PACKAGE IS: HF–PQFN.
4. COPLANARITY APPLIES TO LEADS, CORNER LEADS, AND DIE ATTACH PAD.
5. MIN METAL GAP SHOULD BE 0.2MM.

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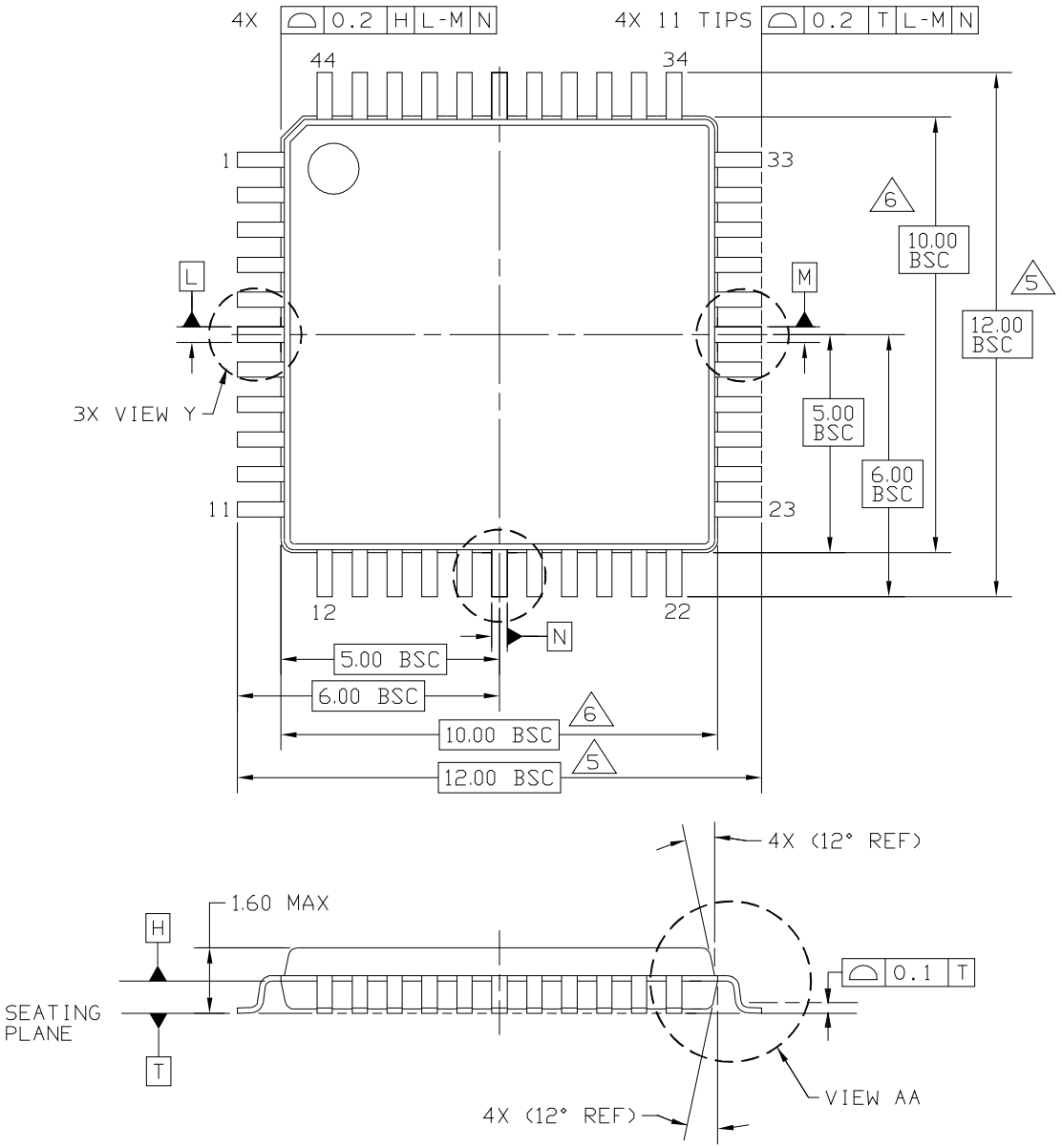
TITLE: THERMALLY ENHANCED QUAD FLAT NON–LEADED PACKAGE (QFN) 48 TERMINAL, 0.5 PITCH (7 X 7 X 1)	DOCUMENT NO: 98ARH99048A	REV: F
	CASE NUMBER: 1314–05	05 DEC 2005
	STANDARD: JEDEC–MO–220 VKKD–2	

Figure 32. 48-pin QFN Package Drawing (Case 1314, Doc #98ARH99048A), Sheet 3 of 3



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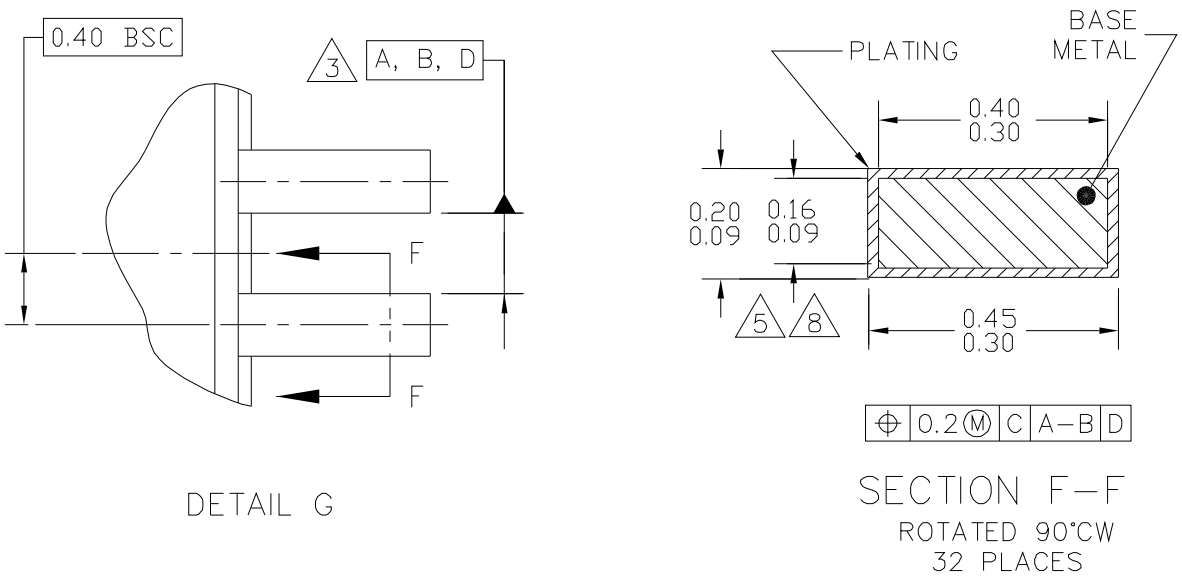
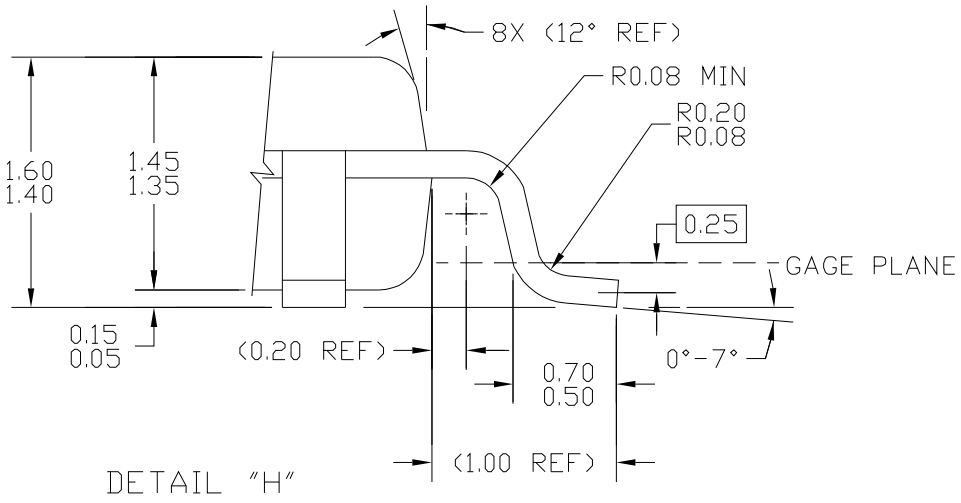
TITLE: 44 LD LQFP, 10 X 10 PKG, 0.8 PITCH, 1.4 THICK	DOCUMENT NO: 98ASS23225W	REV: D
	CASE NUMBER: 824D-02	26 FEB 2007
	STANDARD: JEDEC MS-026-BCB	

Figure 33. 44-pin LQFP Package Drawing (Case 824D, Doc #98ASS23225W), Sheet 1 of 3





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TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	DOCUMENT NO: 98ASH70029A	REV: D
	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

Figure 37. 32-pin LQFP Package Drawing (Case 873A, Doc #98ASH70029A), Sheet 2 of 3